

v00.1014



The HMC618ALP3E is ideal for:

- Cellular/3G and LTE/WiMAX/4G
- BTS & Infrastructure
- Repeaters and Femto Cells
- Public Safety Radios

#### **Functional Diagram**



#### **Electrical Specifications** $T_A = +25^{\circ}$ C, Rbias = 470 Ohm for Vdd1 = Vdd2 = 5V

# HMC618ALP3E

## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### Features

Noise Figure: 0.75 dB Gain: 19 dB OIP3: 36 dBm Single Supply: +3V to +5V 50 Ohm Matched Input/Output 16 Lead 3x3mm SMT Package: 9 mm<sup>2</sup>

#### **General Description**

The HMC618ALP3E is a GaAs pHEMT MMIC Low Noise Amplifier that is ideal for Cellular/3G and LTE/WiMAX/4G basestation front-end receivers operating between 1.2 - 2.2 GHz. The amplifier has been optimized to provide 0.75 dB noise figure, 19 dB gain and +36 dBm output IP3 from a single supply of +5V. Input and output return losses are excellent and the LNA requires minimal external matching and bias decoupling components. The HMC618ALP3E shares the same package and pinout with the HMC617LP3E 0.55 - 1.2 GHz LNA. The HMC618ALP3E can be biased with +3V to +5V and features an externally adjustable supply current which allows the designer to tailor the linearity performance of the LNA for each application. The HMC618ALP3E offers improved noise figure versus the previously released HMC375LP3(E) and the HMC382LP3(E).

<b>D</b>		Vdd = 5 Vdc								
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		1200 - 170	0		1700 - 200	0	2	2000 - 220	C	MHz
Gain	19	23		16	19		13.5	17		dB
Gain Variation Over Temperature		0.012			0.008			0.008		dB/°C
Noise Figure		0.65	0.85		0.75	1.1		0.85	1.15	dB
Input Return Loss		22.5			18			19.5		dB
Output Return Loss		13			12.5			10		dB
Output Power for 1 dB Compression (P1dB)		19		16.5	20		18	20		dBm
Saturated Output Power (Psat)		20.5			20.5			20.5		dBm
Output Third Order Intercept (IP3)	29.4	33.5		29.5	35		30.4	35.5		dBm
Supply Current (Idd)		89	118		89	118		89	118	mA

\* Rbias resistor sets current, see application circuit herein

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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### **Electrical Specifications**



Parameter				,	Vdd = 3 Vd	/dc				
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		1200 - 170	D		1700 - 200	C	2	2000 - 220	0	MHz
Gain	18	22		15	18		12.5	15.8		dB
Gain Variation Over Temperature		0.009			0.009			0.009		dB/°C
Noise Figure		0.8	1.1		0.9	1.2		0.9	1.2	dB
Input Return Loss		26			17			19		dB
Output Return Loss		14			13			11		dB
Output Power for 1 dB Compression (P1dB)	10	15		12	15		13	15		dBm
Saturated Output Power (Psat)		16			16			16		dBm
Output Third Order Intercept (IP3)		28			28			28		dBm
Supply Current (Idd)		47	65		47	65		47	65	mA

\* Rbias resistor sets current, see application circuit herein

#### 1700 to 2200 MHz Tune

#### Broadband Gain & Return Loss<sup>[1][2]</sup>



#### Gain vs. Temperature [2]



[1] Vdd = 5V, Rbias = 470 Ohm [2] Vdd = 3V, Rbias = 10K Ohm

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#### Gain vs. Temperature [1]



#### Input Return Loss vs. Temperature [1]





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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

# ROHS EARTH FRIEND





Noise Figure vs Temperature [1] [2] [3]



#### Psat vs. Temperature [1] [2]



Vdd = 5V, Rbias = 470 Ohm
Vdd = 3V, Rbias = 10K Ohm
Measurement reference plane shown on evaluation PCB drawing.

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Output P1dB vs. Temperature [1] [2]









#### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

1700 to 2200 MHz Tune

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#### Output IP3 and Idd vs. Supply Voltage @ 2100 MHz <sup>[1]</sup>



Power Compression @ 1700 MHz [1]



[1] Vdd = 5V, Rbias = 470 Ohm [2] Vdd = 3V, Rbias = 10K Ohm

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#### Output IP3 and Idd vs. Supply Voltage @ 2100 MHz <sup>[2]</sup>



Power Compression @ 1700 MHz [2]







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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

1700 to 2200 MHz Tune



Gain, Power & Noise Figure vs. Supply Voltage @ 1700 MHz <sup>[1]</sup>



Gain, Power & Noise Figure vs. Supply Voltage @ 2100 MHz <sup>[1]</sup>



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Gain, Power & Noise Figure vs. Supply Voltage @ 1700 MHz<sup>[2]</sup>



Gain, Power & Noise Figure vs. Supply Voltage @ 2100 MHz<sup>[2]</sup>





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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### 1700 to 2200 MHz Tune



Output IP3 vs. Rbias @ 2100 MHz



Gain, Noise Figure vs. Rbias @ 1700 MHz 22 21 NOISE FIGURE 20 0.8 GAIN (dB) ≻ 0.6 19 0.4 18 (dB) 0.2 17 16 0 100 1000 10000 Rbias(Ohms) Vdd=3V Vdd=5V

Gain, Noise Figure vs. Rbias @ 2100 MHz



#### [1] Vdd = 5V, Rbias = 470 Ohm [2] Vdd = 3V, Rbias = 10K Ohm

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#### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

ROHSV EARTH FRIENDLY

#### 1200 to 1700 MHz Tune



Input Return Loss vs. Temperature [1]



Output Return Loss vs. Temperature [1]



[1] Vdd = 5V, Rbias = 470 Ohm [2] Vdd = 3V, Rbias = 10K Ohm

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Input Return Loss vs. Temperature [2]



Output Return Loss vs. Temperature [2]





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#### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### 1200 to 1700 MHz Tune



Noise Figure vs. Temperature [1]



#### Output P1dB vs. Temperature [1]



[1] Vdd = 5V, Rbias = 470 Ohm [2] Vdd = 3V, Rbias = 10K Ohm

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Output P1dB vs. Temperature [2]



RoHS

## HMC618ALP3E

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#### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

1200 to 1700 MHz Tune



#### Absolute Bias Resistor Range & Recommended Bias Resistor Values for Idd

_	<b>J</b>					
	) (dd1 - ) (dd0 () ()					
	Vdd1 = Vdd2 (V)	Min (Ohms) Max (Ohms)		R1 (Ohms)	Idd1 + Idd2 (mA)	
				1k	28	
	3V	1K <sup>[3]</sup>	Open Circuit 1.5k 10k	1.5k	34	
				10k	47	
				120	71	
	5V	0	Open Circuit 270 470	270	84	
				470	89	

[1] Vdd = 5V, Rbias = 470 Ohm
[2] Vdd = 3V, Rbias = 10K Ohm
[3] With Vdd= 3V and Rbias < 1K Ohm may result in the part becoming conditionally stable which is not recommended.</li>

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#### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2)	+6V
RF Input Power (RFIN) (Vdd = +5 Vdc)	+10 dBm
Channel Temperature	150 °C
Continuous Pdiss (T= 85 °C) (derate 9.68 mW/°C above 85 °C)	0.63 W
Thermal Resistance (channel to ground paddle)	103.4 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A, Passed 250V

#### Typical Supply Current vs. Vdd Rbias = 10 KOhm for 3V Rbias = 470 Ohm for 5V

	• •
Vdd (Vdc)	ldd (mA)
2.7	35
3.0	47
3.3	58
4.5	72
5.0	89
5.5	106

Note: Amplifier will operate over full voltage ranges shown above.



#### ELECTROSTATIC SENSITIVE DEVICE **OBSERVE HANDLING PRECAUTIONS Outline Drawing**

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#### NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RE GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

#### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[2]</sup>
HMC618LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[1]</sup>	<u>618</u> XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

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GaAs SMT pHEMT LOW NOISE

AMPLIFIER, 1.2 - 2.2 GHz

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# 

#### **Pin Description**

Pin Number	Function	Description	Interface Schematic
1, 3 - 5, 7, 9, 12, 14, 16	N/C	No connection required. These pins may be connected to RF/DC ground without affecting performance.	
2	RFIN	This pin is DC coupled and matched to 50 Ohms.	
6, 10	GND	This pin and ground paddle must be connected to RC/DC ground.	
8	RES	This pin is used to set the DC current of the amplifier by selection of the external bias resistor. See application circuit.	
11	RFOUT	This pin is matched to 50 Ohms.	
13, 15	Vdd2, Vdd1	Power Supply Voltage for the amplifier. External bypass capacitors of 1000 pF, and 0.47 μF are required.	Vdd1, Vdd2

#### Application Circuit, 1700 to 2200 MHz Tune



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### GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz



#### Evaluation PCB, 1700 to 2200 MHz Tune

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#### **Evaluation PCB Ordering Information**

Item	Content	Part Number
Evaluation PCB	HMC618ALP3E Evaluation PCB	EV2HMC618ALP3

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

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#### List of Materials for Evaluation PCB

Item	Description	
J1, J2	PCB Mount SMA RF Connector	
J3 - J5	DC Pin	
C2, C4	1000 pF Capacitor, 0603 Pkg	
C3, C5	0.47 µF Capacitor, Tantalum	
L1	15 nH, Inductor, 0603 Pkg.	
L3	6.8 nH, Inductor, 0603 Pkg.	
C6	220 pF Capacitor, 0402 Pkg.	
C1	10 nF Capacitor, 0402 Pkg.	
R1	470 Ohm resistor, 0402 Pkg.	
U1	HMC618LP3(E) Amplifier	
PCB [2]	120586 Evaluation PCB	

[1] Reference this number when ordering complete evaluation PCB



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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### Application Circuit, 1200 to 1700 MHz Tune



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## GaAs SMT pHEMT LOW NOISE AMPLIFIER, 1.2 - 2.2 GHz

#### Evaluation PCB, 1200 to 1700 MHz Tune



#### **Evaluation PCB Ordering Information**

Item	Content	Part Number
Evaluation PCB	HMC618ALP3E Evaluation PCB	EV1HMC618ALP3

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

#### List of Materials for Evaluation PCB

Description	
PCB Mount SMA RF Connector	
DC Pin	
10 nF Capacitor, 0402 Pkg.	
1000 pF Capacitor, 0603 Pkg	
0.47 μF Capacitor, 0603 Pkg.	
100 pF Capacitor, 0402 Pkg.	
3 pF Capacitor, 0402 Pkg.	
27 nH, Inductor, 0603 Pkg.	
5.6 nH, Inductor, 0603 Pkg.	
18 nH, Inductor, 0603 Pkg.	
470 Ohm resistor, 0402 Pkg.	
HMC618LP3(E) Amplifier	
600-00077-00 Evaluation PCB	

[1] Circuit Board Material: Rogers 4350.

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